Electronic Supplementary Material (ESI) for Sustainable Energy & Fuels.

Enhancing thermoelectric performance of band structure engineered $GeSe_{1-x}Te_x$ alloys

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Supplementary material

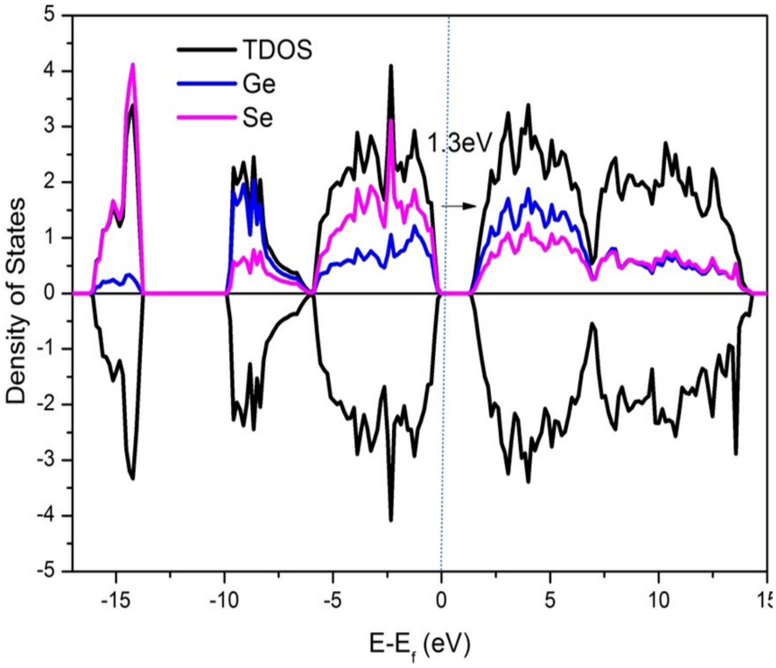

Figure S1 Total and Partial Density of states of GeSe calculated using HSE06 level of theory